STW54NK30Z

N-CHANNEL 300V - 0.052Ω - 54A TO-247
Zener-Protected SuperMESH™ MOSFET

Table 1: General Features

TYPE	BV_{DSS}	$R_{DS(on)}$	I_D	Pw
STW54NK30Z	300 V	< 0.060 Ω	54 A	300 W

- TYPICAL R_{DS}(on) = 0.052 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATIBILITY

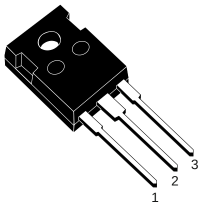
DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING DC CHOPPERs
- IDEAL FOR OFF-LINE POWER SUPPLIES, ADAPTORS AND PFC

Figure 1: Package



TO-247

Figure 2: Internal Schematic Diagram

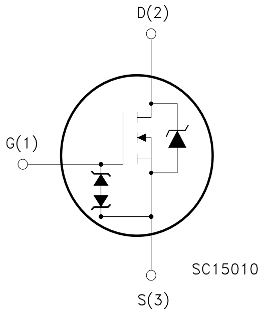


Table 2: Order Codes

SALES TYPE	MARKING	PACKAGE	PACKAGING
STW54NK30Z	W54NK30Z	TO-247	TUBE

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	300	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	300	V
V_{GS}	Gate- source Voltage	± 30	V
I_D	Drain Current (continuous) at T_C = 25°C	54	A
I_D	Drain Current (continuous) at T_C = 100°C	34	A
I_{DM} (•)	Drain Current (pulsed)	200	A
P_{TOT}	Total Dissipation at T_C = 25°C	300	W
	Derating Factor	2.38	W/°C
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=1.5KΩ)	6000	V
dv/dt (1)	Peak Diode Recovery voltage slope	4.5	V/ns
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 150	°C

(●) Pulse width limited by safe operating area
(1) $I_{SD} \leq 54A$, di/dt $\leq 200A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX.}$
(*) Limited only by maximum temperature allowed

Table 4: Thermal Data

Rthj-case	Thermal Resistance Junction-case Max	0.42	°C/W
Rthj-amb T_l	Thermal Resistance Junction-ambient Max Maximum Lead Temperature For Soldering Purpose	30 300	°C/W °C

Table 5: Avalanche Characteristics

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	54	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	400	mJ

Table 6: Gate-Source Zener Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	Igs=± 1mA (Open Drain)	30			V

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)

Table 7: On/Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0	300			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating, T_C = 125 °C			1 50	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 150 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 27 A		0.052	0.060	Ω

Table 8: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} = 15 V, I_D = 27 A		25		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		4960 745 186		pF pF pF
$C_{oss\ eq.}$ (3)	Equivalent Output Capacitance	V_{GS} = 0V, V_{DS} = 0V to 240 V		550		pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on Delay Time Rise Time Turn-off Delay Time Fall Time	V_{DD} = 150 V, I_D = 27 A R_G = 4.7Ω V_{GS} = 10 V (Resistive Load see, Figure 3)		40 45 116 35		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 240V, I_D = 54A, V_{GS} = 10V		158 30 90	221	nC nC nC

Table 9: Source Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (2)	Source-drain Current Source-drain Current (pulsed)				54 200	A A
V_{SD} (1)	Forward On Voltage	I_{SD} = 54 A, V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 54 A, di/dt = 100A/µs V_{DD} = 100 V, T_j = 25°C (see test circuit, Figure 5)		328 2.8 17.2		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 54 A, di/dt = 100A/µs V_{DD} = 100 V, T_j = 150°C (see test circuit, Figure 5)		416 4.2 20.2		ns µC A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.
3. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Figure 3: Safe Operating Area

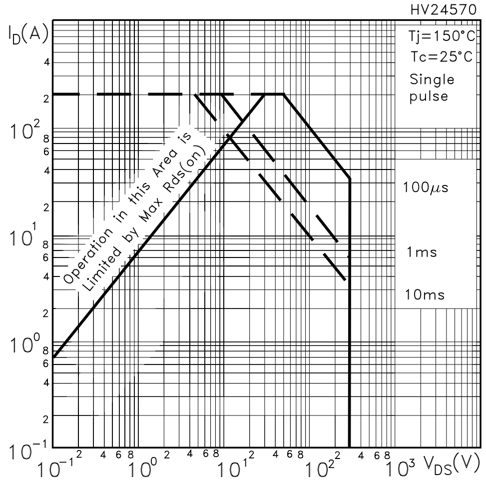


Figure 6: Thermal Impedance

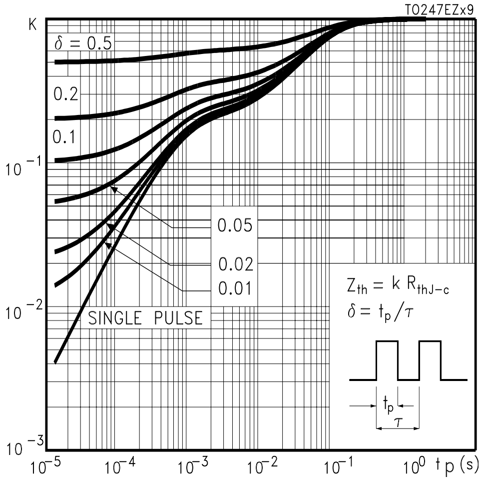


Figure 4: Output Characteristics

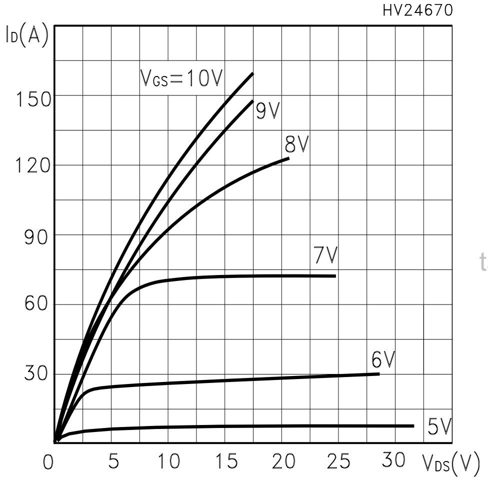


Figure 7: Transfer Characteristics

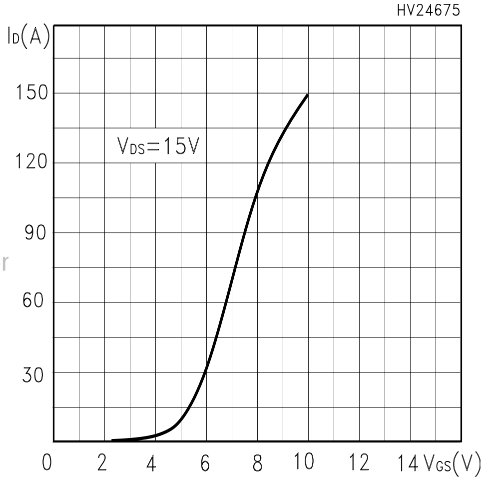


Figure 5: Transconductance

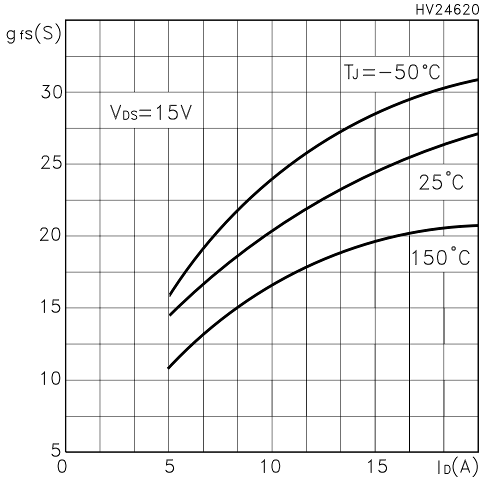


Figure 8: Static Drain-source On Resistance

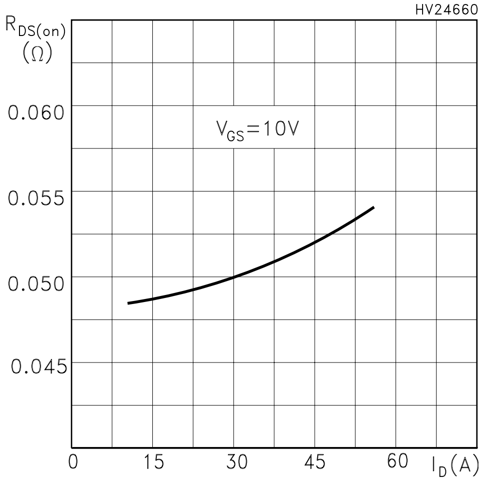


Figure 9: Gate Charge vs Gate-source Voltage

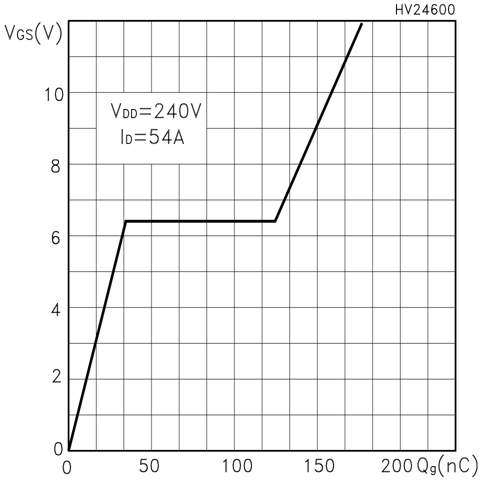


Figure 10: Normalized Gate Thereshold Voltage vs Temperature

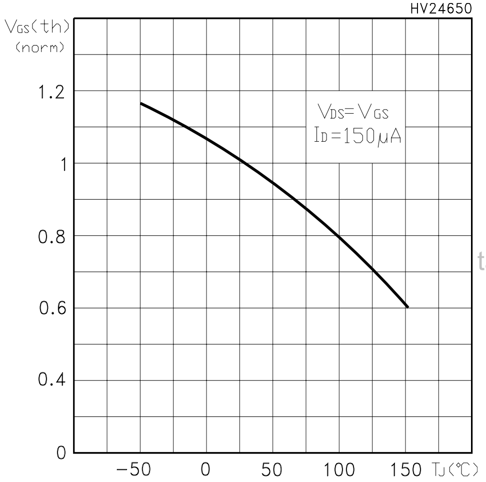


Figure 11: Source-Drain Diode Forward Characteristics

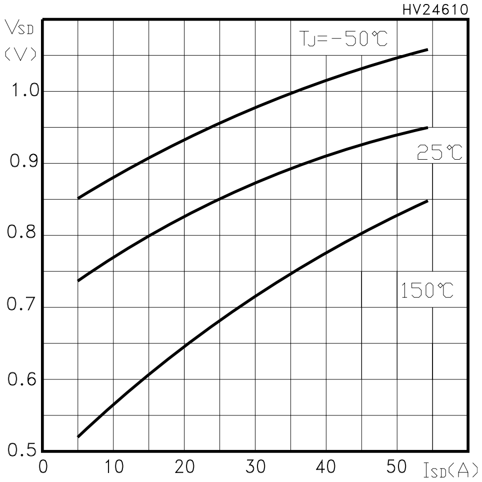


Figure 12: Capacitance Variations

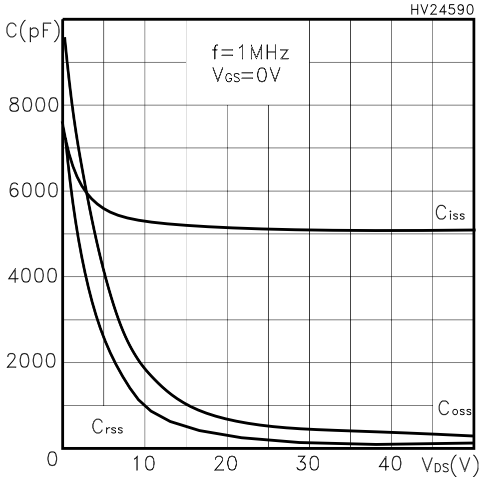


Figure 13: Normalized On Resistance vs Temperature

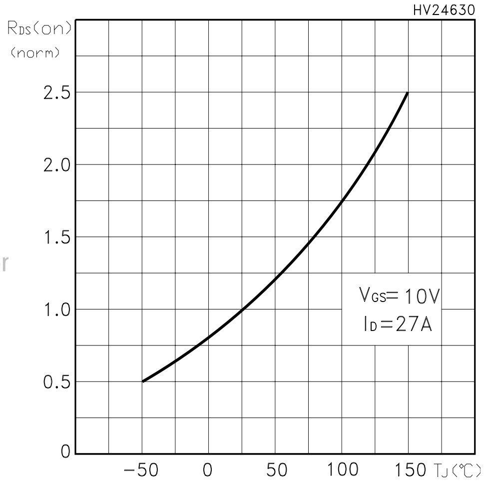


Figure 14: Normalized BVdss vs Temperature

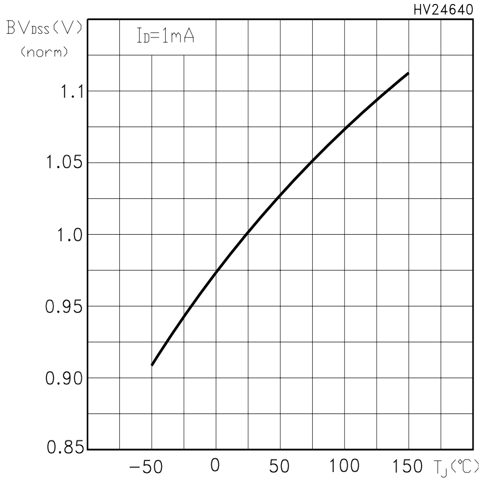


Figure 15: Avalanche Energy vs Starting Tj

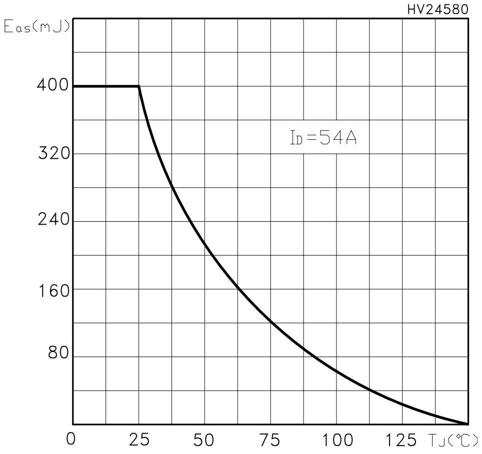


Figure 16: Unclamped Inductive Load Test Circuit

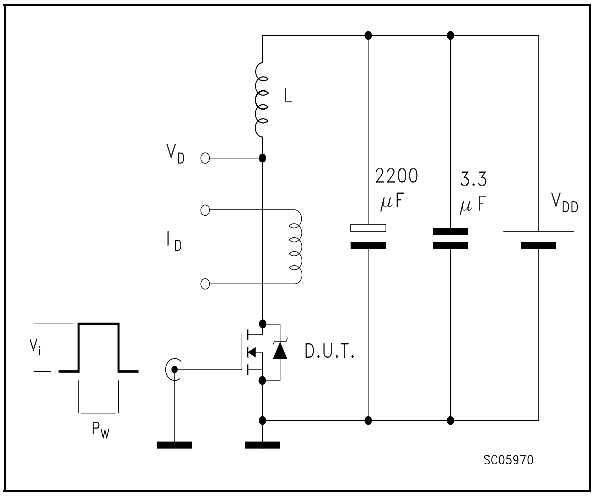


Figure 17: Switching Times Test Circuit For Resistive Load

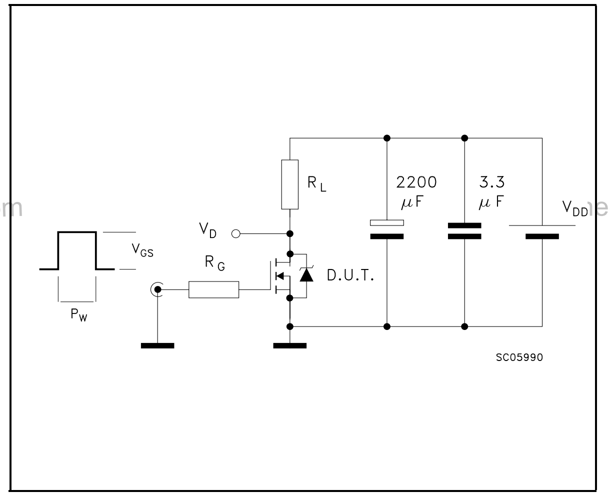


Figure 18: Test Circuit For Inductive Load Switching and Diode Recovery Times

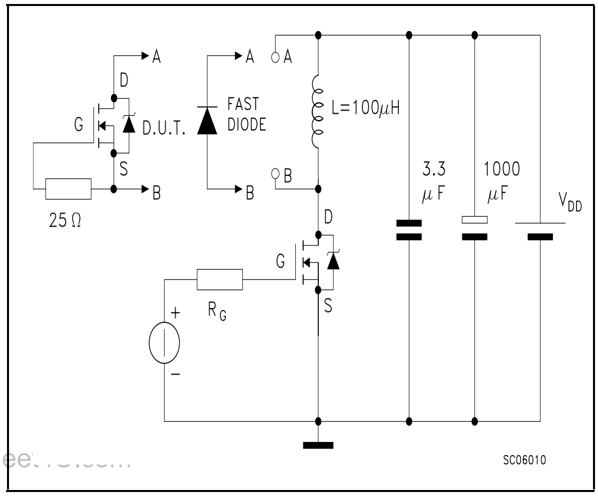


Figure 19: Unclamped Inductive Wafeform

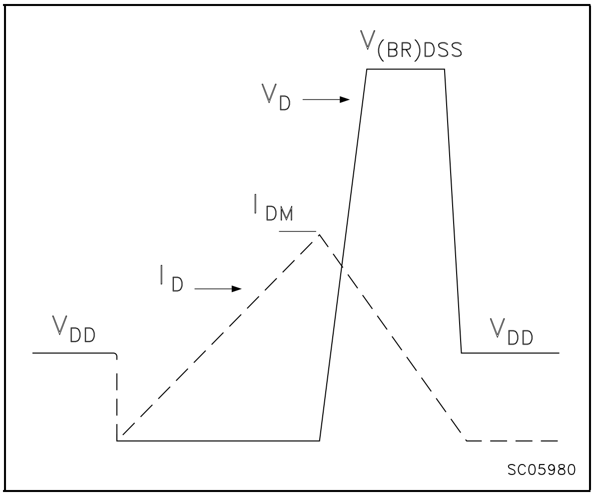
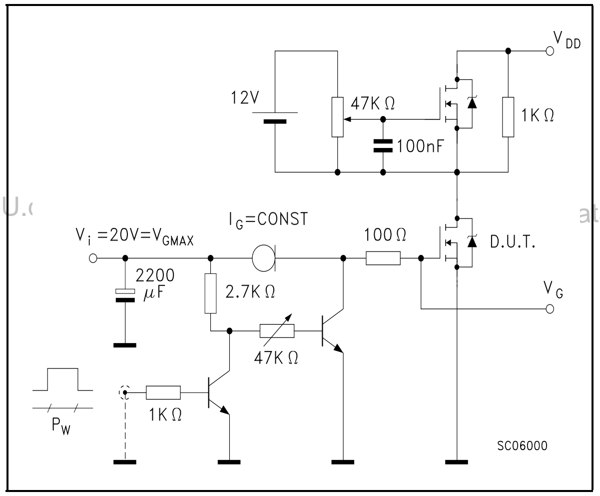


Figure 20: Gate Charge Test Circuit



TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	

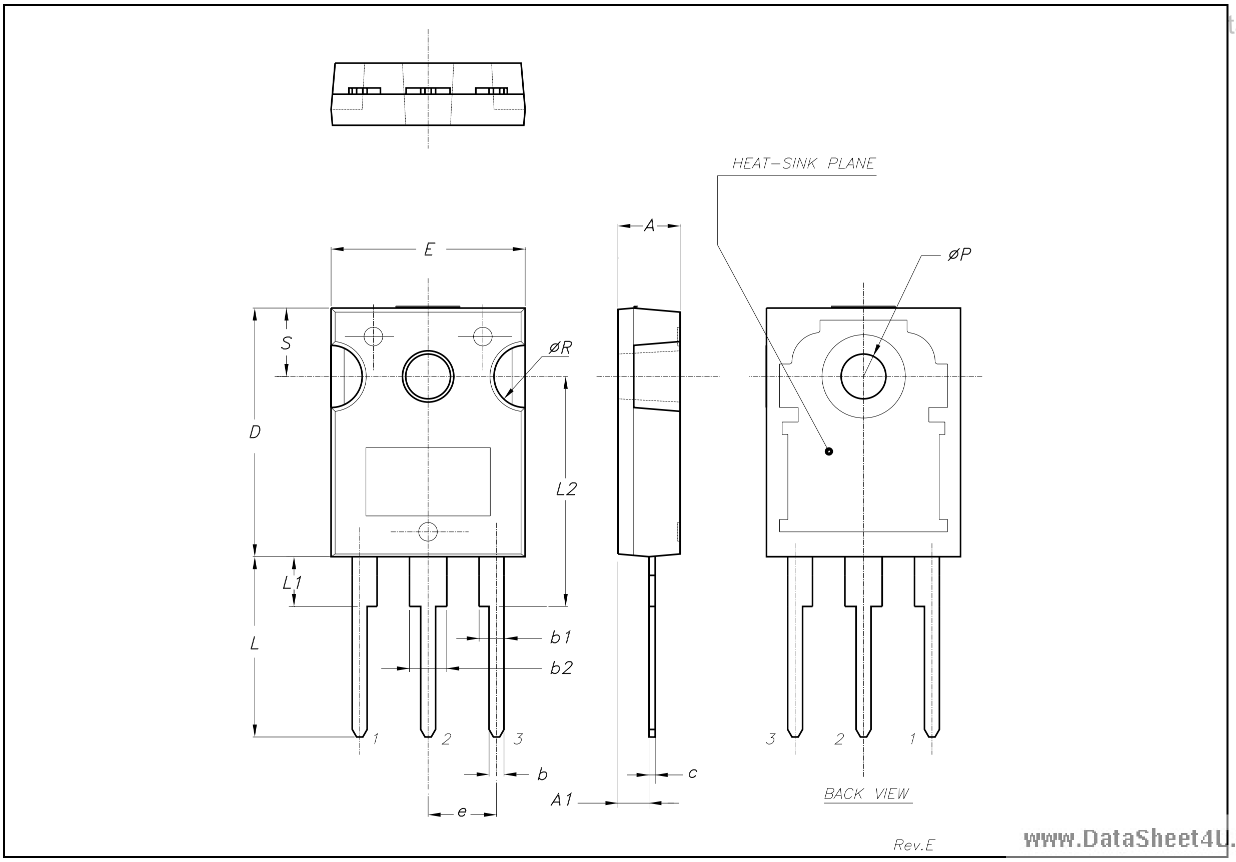


Table 10: Revision History

Date	Revision	Description of Changes
31-Jan-2005	1	Complete datasheet

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Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America